

FEATURES

- For general purpose
- High heat-resistant due to glass passivation.

OUTLINE DRAWING



ABSOLUTE MAXIMUM RATINGS

Items	Туре		DSM3MA1	DSM3MA2	DSM3MA4			
Repetitive Peak Reverse Voltage	V _{RRM}	V	100	200	400			
Average Forward Current	I _{F(AV)}	А	3.0 (Single-phase half sine wave 180° conduction)					
Surge(Non-Repetitive) Forward Current	I _{FSM}	А	80(Without PIV, 10ms, conduction Tj = 40° C start)					
I ² t Limit Value	l ² t	A ² s	25.6(Time = 2 ~ 10ms, I = RMS value)					
Operating Junction Temperature	Tj	°C	-40 ~ +150					
Storage Temperature	T _{stg}	°C	-40 ~ +150					

CHARACTERISTICS(T_L=25°C)

Items	Symbols	Units	Min.	Тур.	Max.	Test Conditions	
Peak Reverse Current	I _{RRM}	μA	_	-	20	DSM3MA1,2	Rated V _{RRM}
					10	DSM3MA4	
Peak Forward Voltage	$V_{\rm FM}$	V	_	_	1.0	I _{FM} =3.0Ap, Single-phase half sine wave 1 cycle	
Steady State Thermal Impedance	R _{th(j-a)}	°C/W	_	_	80	On glass-epoxi substrate (□ 50mm) Soldering land (□ 10mm)	
	R _{th(j-l)}				13		

DSM3MA

Forward characteristics







Max. average forward power dissipation (Resistive or inductive load)



Transient thermal impedance



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HITACHI POWER SEMICONDUCTORS

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